Abstracts

High Reliability Power GaAs MESFET Under RF Overdrive Condition

---

H. Hasegawa, K. Katsukawa, T. Itoh, T. Noguchi and Y. Kaneko. "High Reliability Power GaAs MESFET Under RF Overdrive Condition." 1993 MTT-S International Microwave Symposium Digest 93.1 (1993 Vol. I [MWSYM]): 289-292.

This paper reports on high reliability high power GaAs MESFETs with SiO/sub 2/ passivation film. For these MESFETs, no degradation has been observed up to 1500 hours even under 8 dB gain compression condition.

❑ Return to main document.